

## FDH15N50 / FDP15N50 / FDB15N50

### 15A, 500V, 0.38 Ohm, N-Channel SMPS Power MOSFET

#### Applications

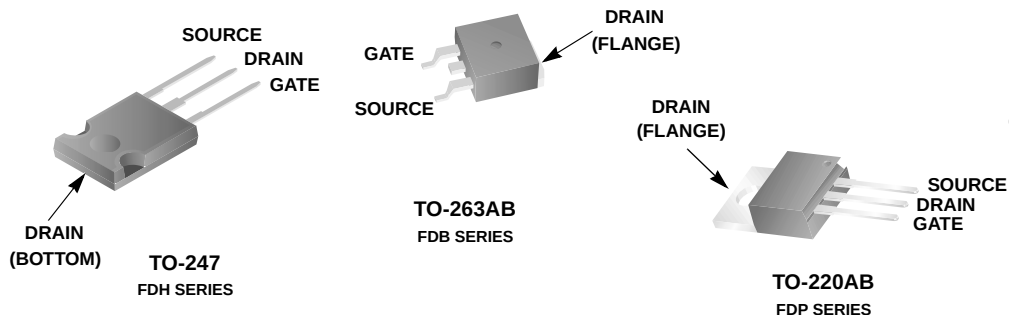
##### Switch Mode Power Supplies(SMPS), such as

- PFC Boost
- Two-Switch Forward Converter
- Single Switch Forward Converter
- Flyback Converter
- Buck Converter
- High Speed Switching

#### Features

- Low Gate Charge  $Q_g$  results in Simple Drive Requirement
- Improved Gate, Avalanche and High Reapplied  $dv/dt$  Ruggedness
- Reduced  $r_{DS(ON)}$
- Reduced Miller Capacitance and Low Input Capacitance
- Improved Switching Speed with Low EMI
- 175°C Rated Junction Temperature

#### Package



#### Symbol

#### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol         | Parameter                                                        | Ratings               | Units               |
|----------------|------------------------------------------------------------------|-----------------------|---------------------|
| $V_{DSS}$      | Drain to Source Voltage                                          | 500                   | V                   |
| $V_{GS}$       | Gate to Source Voltage                                           | $\pm 30$              | V                   |
| $I_D$          | Drain Current                                                    |                       |                     |
|                | Continuous ( $T_C = 25^\circ\text{C}$ , $V_{GS} = 10\text{V}$ )  | 15                    | A                   |
|                | Continuous ( $T_C = 100^\circ\text{C}$ , $V_{GS} = 10\text{V}$ ) | 11                    | A                   |
|                | Pulsed <sup>1</sup>                                              | 60                    | A                   |
| $P_D$          | Power dissipation                                                | 300                   | W                   |
|                | Derate above $25^\circ\text{C}$                                  | 2                     | W/ $^\circ\text{C}$ |
| $T_J, T_{STG}$ | Operating and Storage Temperature                                | -55 to 175            | $^\circ\text{C}$    |
|                | Soldering Temperature for 10 seconds                             | 300 (1.6mm from case) | $^\circ\text{C}$    |

#### Thermal Characteristics

|                 |                                                         |      |                    |
|-----------------|---------------------------------------------------------|------|--------------------|
| $R_{\theta JC}$ | Thermal Resistance Junction to Case                     | 0.50 | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance Junction to Ambient (TO-247)         | 40   | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance Junction to Ambient (TO-220, TO-263) | 62   | $^\circ\text{C/W}$ |

## Package Marking and Ordering Information

| Device Marking | Device   | Package | Reel Size | Tape Width | Quantity |
|----------------|----------|---------|-----------|------------|----------|
| FDH15N50       | FDH15N50 | TO-247  | Tube      | -          | 30       |
| FDP15N50       | FDP15N50 | TO-220  | Tube      | -          | 50       |
| FDB15N50       | FDB15N50 | TO-263  | 330mm     | 24mm       | 800      |

## Electrical Characteristics $T_J = 25^\circ\text{C}$ (unless otherwise noted)

| Symbol                       | Parameter                           | Test Conditions                                         | Min | Typ  | Max       | Units               |
|------------------------------|-------------------------------------|---------------------------------------------------------|-----|------|-----------|---------------------|
| <b>Statics</b>               |                                     |                                                         |     |      |           |                     |
| $B_{VDSS}$                   | Drain to Source Breakdown Voltage   | $I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$           | 500 | -    | -         | V                   |
| $\Delta B_{VDSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient | Reference to $25^\circ\text{C}$ ,<br>$I_D = 1\text{mA}$ | -   | 0.58 | -         | V/ $^\circ\text{C}$ |
| $r_{DS(ON)}$                 | Drain to Source On-Resistance       | $V_{GS} = 10\text{V}$ , $I_D = 7.5\text{A}$             | -   | 0.33 | 0.38      | $\Omega$            |
| $V_{GS(th)}$                 | Gate Threshold Voltage              | $V_{DS} = V_{GS}$ , $I_D = 250\mu\text{A}$              | 2.0 | 3.4  | 4.0       | V                   |
| $I_{DSS}$                    | Zero Gate Voltage Drain Current     | $V_{DS} = 500\text{V}$ , $T_C = 25^\circ\text{C}$       | -   | -    | 25        | $\mu\text{A}$       |
|                              |                                     | $V_{GS} = 0\text{V}$ , $T_C = 150^\circ\text{C}$        | -   | -    | 250       |                     |
| $I_{GSS}$                    | Gate to Source Leakage Current      | $V_{GS} = \pm 30\text{V}$                               | -   | -    | $\pm 100$ | nA                  |

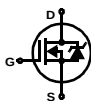
## Dynamics

|              |                               |                                                                     |    |      |    |    |
|--------------|-------------------------------|---------------------------------------------------------------------|----|------|----|----|
| $g_{fs}$     | Forward Transconductance      | $V_{DD} = 10\text{V}$ , $I_D = 7.5\text{A}$                         | 10 | -    | -  | S  |
| $Q_{g(TOT)}$ | Total Gate Charge at 10V      | $V_{GS} = 10\text{V}$ ,                                             | -  | 33   | 41 | nC |
| $Q_{gs}$     | Gate to Source Gate Charge    | $V_{DS} = 400\text{V}$ ,                                            | -  | 7.2  | 10 | nC |
| $Q_{gd}$     | Gate to Drain "Miller" Charge | $I_D = 15\text{A}$                                                  | -  | 12   | 16 | nC |
| $t_{d(ON)}$  | Turn-On Delay Time            | $V_{DD} = 250\text{V}$ ,                                            | -  | 9    | -  | ns |
| $t_r$        | Rise Time                     | $I_D = 15\text{A}$ ,                                                | -  | 5.4  | -  | ns |
| $t_{d(OFF)}$ | Turn-Off Delay Time           | $R_G = 6.2\Omega$ ,                                                 | -  | 26   | -  | ns |
| $t_f$        | Fall Time                     | $R_D = 17\Omega$                                                    | -  | 5    | -  | ns |
| $C_{ISS}$    | Input Capacitance             | $V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$ ,<br>$f = 1\text{MHz}$ | -  | 1850 | -  | pF |
| $C_{OSS}$    | Output Capacitance            |                                                                     | -  | 230  | -  | pF |
| $C_{RSS}$    | Reverse Transfer Capacitance  |                                                                     | -  | 16   | -  | pF |

## Avalanche Characteristics

|          |                                            |     |   |    |    |
|----------|--------------------------------------------|-----|---|----|----|
| $E_{AS}$ | Single Pulse Avalanche Energy <sup>2</sup> | 760 | - | -  | mJ |
| $I_{AR}$ | Avalanche Current                          | -   | - | 15 | A  |

## Drain-Source Diode Characteristics

|          |                                                    |                                                                                                                                                        |   |      |     |               |
|----------|----------------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------|---|------|-----|---------------|
| $I_S$    | Continuous Source Current<br>(Body Diode)          | MOSFET symbol showing the integral reverse p-n junction diode.<br> | - | -    | 15  | A             |
| $I_{SM}$ | Pulsed Source Current <sup>1</sup><br>(Body Diode) |                                                                                                                                                        | - | -    | 60  | A             |
| $V_{SD}$ | Source to Drain Diode Voltage                      | $I_{SD} = 15\text{A}$                                                                                                                                  | - | 0.86 | 1.2 | V             |
| $t_{rr}$ | Reverse Recovery Time                              | $I_{SD} = 15\text{A}$ , $di_{SD}/dt = 100\text{A}/\mu\text{s}$                                                                                         | - | 470  | 730 | ns            |
| $Q_{RR}$ | Reverse Recovered Charge                           | $I_{SD} = 15\text{A}$ , $di_{SD}/dt = 100\text{A}/\mu\text{s}$                                                                                         | - | 5    | 6.6 | $\mu\text{C}$ |

### Notes:

1: Repetitive rating; pulse width limited by maximum junction temperature

2: Starting  $T_J = 25^\circ\text{C}$ ,  $L = 7.0\text{mH}$ ,  $I_{AS} = 15\text{A}$

## Typical Characteristics

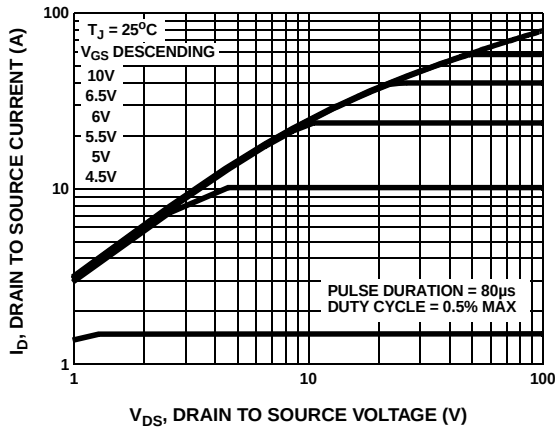


Figure 1. Output Characteristics

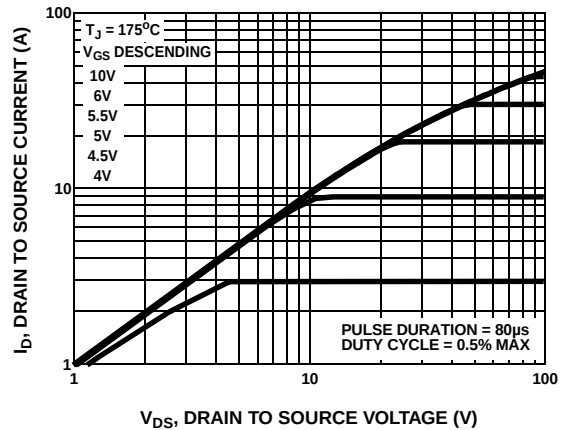


Figure 2. Output Characteristics

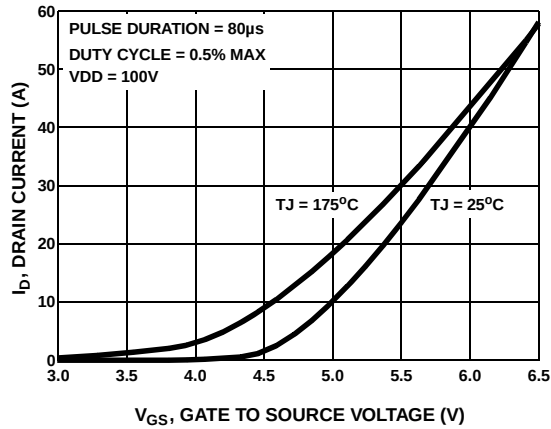


Figure 3. Transfer Characteristics

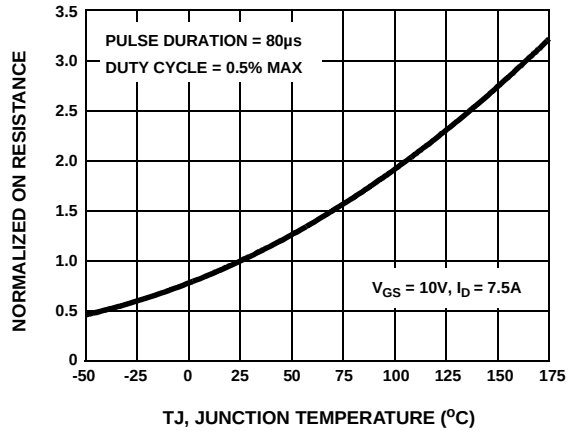


Figure 4. Normalized Drain To Source On Resistance vs Junction Temperature

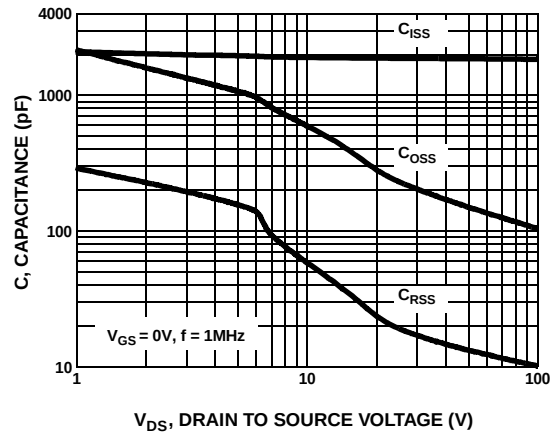


Figure 5. Capacitance vs Drain To Source Voltage

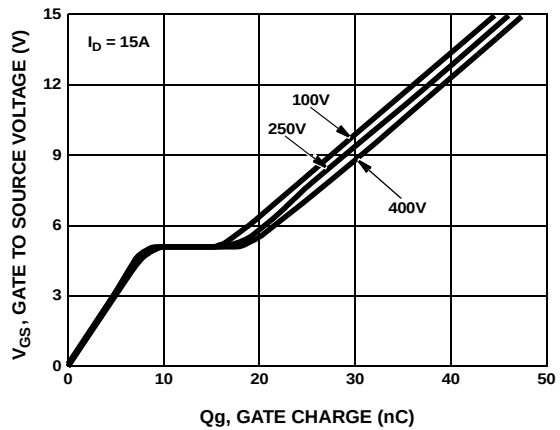


Figure 6. Gate Charge Waveforms For Constant Gate Current

## Typical Characteristics

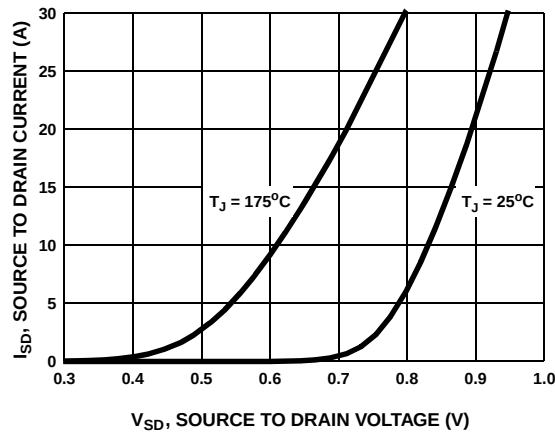


Figure 7. Body Diode Forward Voltage vs Body Diode Current

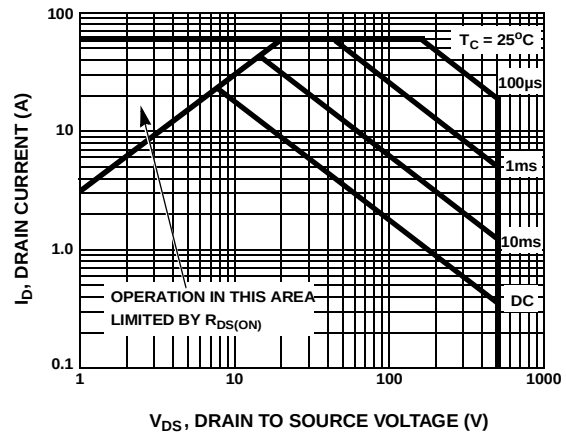


Figure 8. Maximum Safe Operating Area

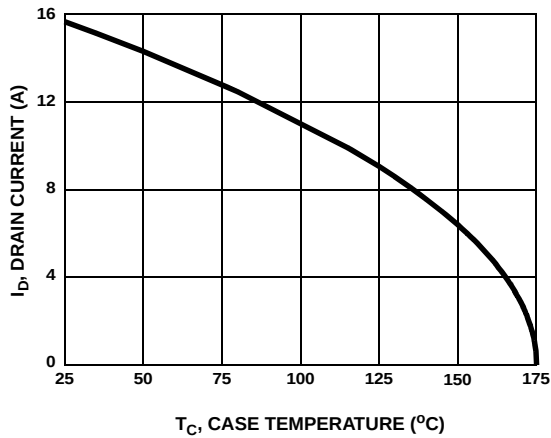


Figure 9. Maximum Drain Current vs Case Temperature

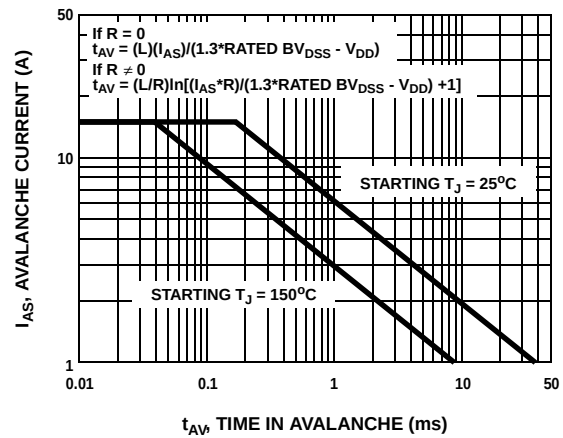


Figure 10. Unclamped Inductive Switching Capability

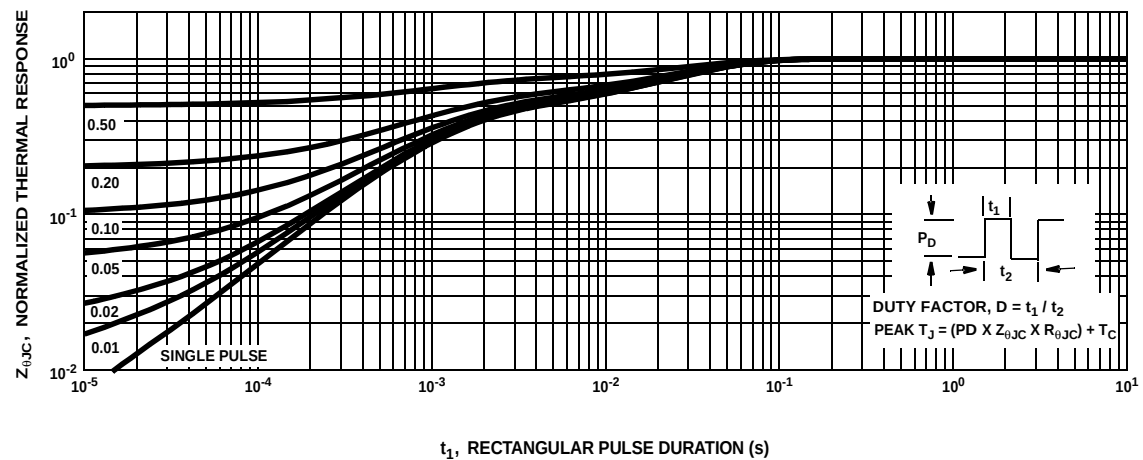


Figure 11. Normalized Transient Thermal Impedance, Junction to Case

## Test Circuits and Waveforms

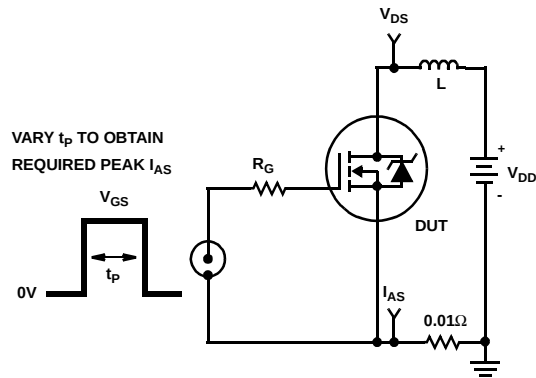


Figure 12. Unclamped Energy Test Circuit

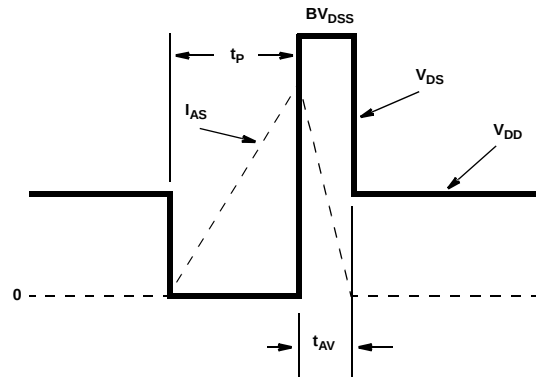


Figure 13. Unclamped Energy Waveforms

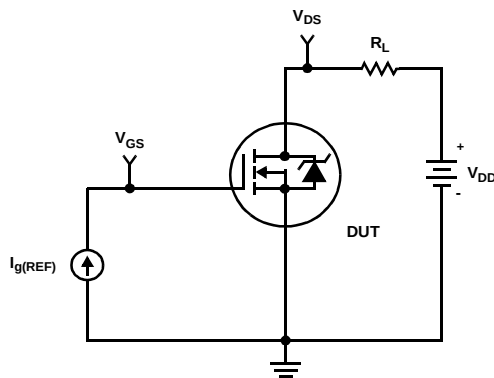


Figure 14. Gate Charge Test Circuit

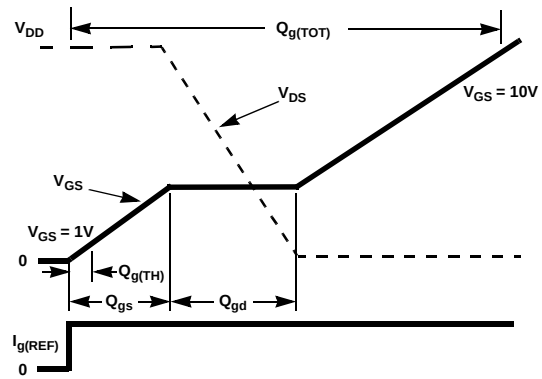


Figure 15. Gate Charge Waveforms

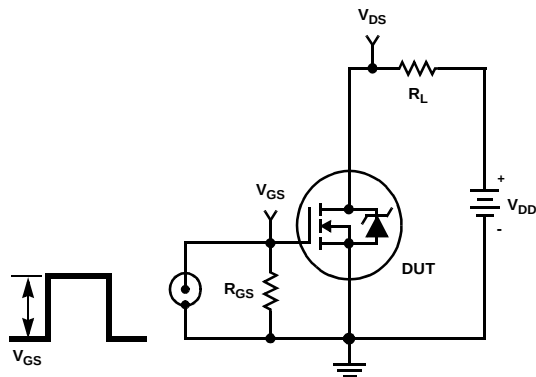


Figure 16. Switching Time Test Circuit

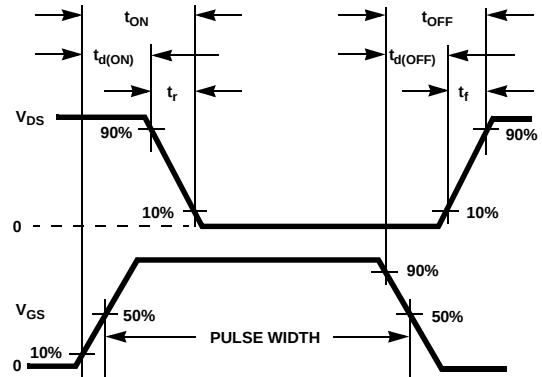


Figure 17. Switching Time Waveform

## TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

|                                      |                     |                    |                     |                 |
|--------------------------------------|---------------------|--------------------|---------------------|-----------------|
| ACE <sup>x</sup> ™                   | FACT™               | ImpliedDisconnect™ | PACMAN™             | SPM™            |
| ActiveArray™                         | FACT Quiet Series™  | ISOPLANAR™         | POP™                | Stealth™        |
| Bottomless™                          | FAST®               | LittleFET™         | Power247™           | SuperSOT™-3     |
| CoolFET™                             | FASTr™              | MicroFET™          | PowerTrench®        | SuperSOT™-6     |
| CROSSVOLT™                           | FRFET™              | MicroPak™          | QFET®               | SuperSOT™-8     |
| DOME™                                | GlobalOptoisolator™ | MICROWIRE™         | QS™                 | SyncFET™        |
| EcoSPARK™                            | GTO™                | MSX™               | QT Optoelectronics™ | TinyLogic®      |
| E <sup>2</sup> CMOS™                 | HiSeC™              | MSXPro™            | Quiet Series™       | TruTranslation™ |
| EnSigna™                             | I <sup>2</sup> C™   | OCX™               | RapidConfigure™     | UHC™            |
| Across the board. Around the world.™ |                     | OCXPro™            | RapidConnect™       | UltraFET®       |
| The Power Franchise™                 |                     | OPTOLOGIC®         | SILENT SWITCHER®    | VCX™            |
| Programmable Active Droop™           |                     | OPTOPLANAR™        | SMART START™        |                 |

## DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

## LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

## PRODUCT STATUS DEFINITIONS

### Definition of Terms

| Datasheet Identification | Product Status         | Definition                                                                                                                                                                                                            |
|--------------------------|------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| Advance Information      | Formative or In Design | This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.                                                                                    |
| Preliminary              | First Production       | This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design. |
| No Identification Needed | Full Production        | This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.                                                       |
| Obsolete                 | Not In Production      | This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.                                                   |



**Стандарт  
Электрон  
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

**Наши контакты:**

**Телефон:** +7 812 627 14 35

**Электронная почта:** [sales@st-electron.ru](mailto:sales@st-electron.ru)

**Адрес:** 198099, Санкт-Петербург,  
Промышленная ул, дом № 19, литера Н,  
помещение 100-Н Офис 331